

2SD1327

Silicon NPN Triple-Diffused Planar Darlington Type

Medium Speed Power Switching

■ Features

- 60V Zener diode built-in between C and B
- Very small fluctuation in breakdown voltages
- Large energy handling capability
- High speed switching
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CB0}	60 ± 10	V
Collector-emitter voltage	V_{CE0}	60 ± 10	V
Emitter-base voltage	V_{EB0}	7	V
Peak collector current	I_{CP}	12	A
Collector current	I_C	8	A
Collector power dissipation	Tc = 25 °C	45	W
	Ta = 25 °C	2	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

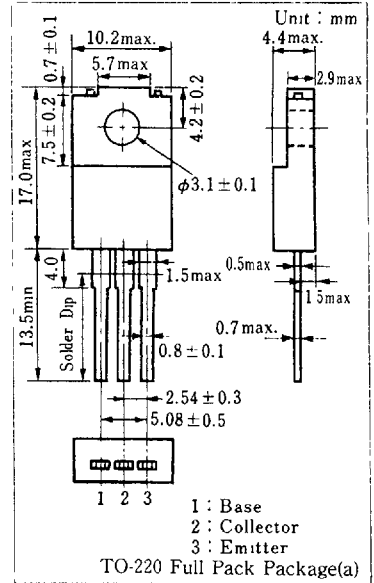
■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CB0}	$V_{CB} = 50 \text{ V}, I_E = 0$			100	μA
Emitter cutoff current	I_{EB0}	$V_{EB} = 7 \text{ V}, I_C = 0$			2	mA
Collector-emitter voltage	V_{CE0}	$I_C = 5 \text{ mA}, I_B = 0$	50		70	V
DC current gain	h_{FE1}^{*1}	$V_{CE} = 3 \text{ V}, I_C = 4 \text{ A}$	1000		10000	
	h_{FE2}	$V_{CE} = 3 \text{ V}, I_C = 8 \text{ A}$	500			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4 \text{ A}, I_B = 8 \text{ mA}$			1.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 4 \text{ A}, I_B = 8 \text{ mA}$			2	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = 4 \text{ A}, I_{B1} = 8 \text{ mA}, I_{B2} = -8 \text{ mA}$ $V_{CC} = 50 \text{ V}$		0.5		μs
Storage time	t_{stg}		4		μs	
Fall time	t_f		1		μs	
Energy handling capability	$E_{s/b}^{*2}$	$I_C = 1 \text{ A}, L = 100 \text{ mH}, R_{BL} = 100 \Omega$	50			mJ

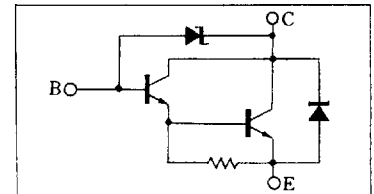
*1 h_{FE1} Classifications

Class	R	Q	P
h_{FE1}	1000 ~ 2500	2000 ~ 5000	4000 ~ 10000

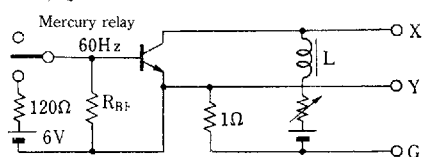
■ Package Dimensions



■ Inner Circuit



*2 E_s, b Test method



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